Diffusion Current Equation In Semiconductor Diode

Elementrix Classes

Diffusion Current Equation in Semiconductor Diode :

$$I_{diffusion} = A imes \left(q D p \, rac{d_p}{d_x} - q D n rac{d_n}{d_x}
ight)$$

The diffusion current density (J_{diffusion}) is a measure of the flow of charge carriers (such as electrons or holes) in a semiconductor material due to concentration gradients.

$$J_{diffusion} = J_e + J_h$$

$$J_e(diffusion) = -qD_nrac{d_n}{d_x}$$

where J_e (diffusion) is the diffusion current density due to electrons.

$$J_h\left(diffusion
ight) = qD_prac{d_p}{d_x}$$

where J_h (diffusion) is the diffusion current density due to holes.

□ **q** is the elementary charge, 1.6 x 10⁻¹⁹. It represents the charge of an electron or hole.

□ **D**_n and **D**_p are the diffusion coefficients, representing how fast electrons and holes move in response to a concentration gradient.

 $\square \frac{d_n}{d_x} and \frac{d_p}{d_x}$ are the gradients of electron and hole concentrations

with respect to position. They indicate how the concentration of carriers changes along the length of the semiconductor.

❑ A represents the cross-sectional area perpendicular to the direction of carrier flow. It represents the area through which charge carriers can move.

□ I_{diffusion} represents the diffusion current.

Example:

Consider a silicon p-n junction diode with the following parameters:

- Electron diffusion coefficient (D_n) = 30 cm²/s
- Hole diffusion coefficient (D_p) = 15 cm²/s
- Electron concentration gradient at the junction $\frac{d_n}{d_r} = -10^{18} cm^{-5}$
- Hole concentration gradient at the junction $rac{d_p}{d_r} = 10^{18} cm^{-5}$
- Elementary charge (q) = 1.602 x 10⁻¹⁹ C
- Cross-sectional area of the junction (A) = 10⁻⁴ cm² (assumed for calculation)

Calculations:

□ Electron Diffusion Current Density $J_e(diffusion) = -qD_n \frac{d_n}{d_x}$

 $J_{e}(diffusion) = - (1.602 \text{ x } 10^{-19} \text{ C}) \text{ x } (30 \text{ cm}^{2}/\text{s}) \text{ x } (-10^{18} \text{ cm}^{-5})$ $= 4.806 \text{ A/cm}^{2}$

□ Hole Diffusion Current Density $J_h(diffusion) = qD_p \frac{d_p}{d_x}$

 $J_{h}(diffusion) = (1.602 \times 10^{-19} \text{ C}) \times (15 \text{ cm}^{2}/\text{s}) \times (10^{18} \text{ cm}^{-5})$

 $= 2.403 \text{ A/cm}^2$

□ Total Diffusion Current Density (J_{diffusion}):

 $J_{diffusion} = J_e + J_h$ = 4.806 A/cm² + 2.403 A/cm² = 7.209 A/cm² Diffusion Current I_{diffusion}: I_{diffusion} = J_{diffusion} x A = 7.209 A/cm² x 10⁻⁴ cm²

= 7.209 x 10⁻⁴ A

I_{diffusion} = 0.729 mA



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